

S4-01P16203

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No.	:	10/549,784	Confirmation No: 3600
Applicant	:	Rudolf Elpelt, et al.	
Filed	:	September 19, 2005	
Title	:	Semiconductor Structure Comprising a Highly Doped Conductive Channel Region and Method for Producing a Semiconductor Structure	
Art Unit	:	2826	
Examiner	:	Scott R. Wilson	
Docket No.	:	S4-01P16203	
Customer No.	:	24131	

Hon. Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

A M E N D M E N T

Sir:

Responsive to the Office action dated November 13, 2008 kindly amend the above-identified application as follows:

- **Amendments to the Claims** begin on page 2 of this paper.
- **Remarks/Arguments** begin on page 8 of this paper.